

IN THE CLAIMS:

1. (Previously Presented) A semiconductor device comprising;
an analog buffer comprising at least one of a current mirror circuit and a differential circuit, the one of the current minor circuit and the differential circuit comprising at least a first and second thin film transistors; and

channel forming regions of the first and second thin film transistors, each of the channel forming regions comprising a polycrystalline semiconductor layer,
wherein a gate length of the first and second thin film transistors is 7 μm or longer.

Cl 2. (Original) A semiconductor device according to claim 1, wherein the device is selected from the group consisting of a liquid crystal display, an EL display, a video camera, a digital camera, a projector, a projection TV, a goggle type display, a navigation system, a sound reproduction device, a note type personal computer, a game device, a portable information terminal, an image playback device having a recording medium.

3. (Previously Presented) A semiconductor device comprising;
an analog buffer comprising at least one of a current mirror circuit and a differential circuit, the one of the current minor circuit and the differential circuit comprising at least a first and second thin film transistors; and

channel forming regions of the first and second thin film transistors, each of the channel forming regions comprising a polycrystalline semiconductor layer,
wherein a gate width of the first and second thin film transistors is 50 μm or longer.

4. (Original) A semiconductor device according to claim 3, wherein the device is selected from the group consisting of a liquid crystal display, an EL display, a video camera, a digital camera, a projector, a projection TV, a goggle type display, a navigation system, a sound reproduction device, a note type personal computer, a game device, a portable information terminal, an image playback device having a recording medium.

5. (Previously Presented) A semiconductor device comprising;
an analog buffer comprising at least one of a current mirror circuit and a differential circuit, the one of the current minor circuit and the differential circuit comprising at least a

first and second thin film transistors; and

channel forming regions of the first and second thin film transistors, each of the channel forming regions comprising a polycrystalline semiconductor layer,

a gate length of the first and second thin film transistors is 7 μm or longer and a gate width of the first and second thin film transistors is 50 μm or longer.

6. (Original) A semiconductor device according to claim 5, wherein the device is selected from the group consisting of a liquid crystal display, an EL display, a video camera, a digital camera, a projector, a projection TV, a goggle type display, a navigation system, a sound reproduction device, a note type personal computer, a game device, a portable information terminal, an image playback device having a recording medium.

7-14. (Cancelled).

15. (Original) A semiconductor device comprising:
an analog buffer comprising at least one of a current mirror circuit and a differential circuit, the one of the current minor circuit and the differential circuit comprising at least a first and second thin film transistors,

wherein each of the first and second thin film transistors has a channel region comprising a polycrystalline semiconductor layer,

wherein a gate length of each of the first and second thin film transistors is 7 μm or longer;

wherein the first and second thin film transistors are connected in parallel with each other; and

wherein a gate electrode of the first thin film transistor and a gate electrode of the second thin film transistor are connected to a same potential.

16. (Original) A semiconductor device according to claim 15, wherein a gate width of the respective thin film transistors is 50 μm or longer.

17. (Original) A semiconductor device according to claim 15, wherein the respective thin film transistors is a multi-gate type.

18. (Currently Amended) A semiconductor device according to claim 15, wherein the respective thin film transistors is a multi-gate type and a gate width of the respective thin film transistors is 50 [μm] or longer.

19. (Original) A semiconductor device according to claim 15, wherein the device is selected from the group consisting of a liquid crystal display, an EL display, a video camera, a digital camera, a projector, a projection TV, a goggle type display, a navigation system, a sound reproduction device, a note type personal computer, a game device, a portable information terminal, an image playback device having a recording medium.

20. (Original) A semiconductor device comprising:

an analog buffer comprising at least one of a current mirror circuit and a differential circuit, the one of the current mirror circuit and the differential circuit comprising at least a first and second thin film transistors,

wherein each of the first and second thin film transistors has a channel region comprising a polycrystalline semiconductor layer,

wherein a gate width of each of the first and second thin film transistors is 50 μm or longer;

wherein the first and second thin film transistors are connected in parallel with each other; and

wherein a gate electrode of the first thin film transistor and a gate electrode of the second thin film transistor are connected to a same potential.

21. (Original) A semiconductor device according to claim 20, wherein the respective thin film transistors is multi-gate type.

22. (Original) A semiconductor device according to claim 20, wherein the device is selected from the group consisting of a liquid crystal display, an EL display, a video camera, a digital camera, a projector, a projection TV, a goggle type display, a navigation system, a sound reproduction device, a note type personal computer, a game device, a portable information terminal, an image playback device having a recording medium.

23. (Original) A semiconductor device comprising:

an analog buffer comprising at least one of a current mirror circuit and a differential circuit, the one of the current mirror circuit and the differential circuit comprising at least a first and second thin film transistors,

wherein each of the first and second thin film transistors has a channel region comprising a polycrystalline semiconductor layer,

wherein each of the first and second thin film transistors is multi-gate type

wherein the first and second thin film transistors are connected in parallel with each other; and

wherein a gate electrode of the first thin film transistor and a gate electrode of the second thin film transistor are connected to a same potential.

24. (Original) A semiconductor device according to claim 23, wherein the device is selected from the group consisting of a liquid crystal display, an EL display, a video camera, a digital camera, a projector, a projection TV, a goggle type display, a navigation system, a sound reproduction device, a note type personal computer, a game device, a portable information terminal, an image playback device having a recording medium.

25. (Original) A semiconductor device comprising:

an analog buffer comprising at least one of a current mirror circuit and a differential circuit, the one of the current mirror circuit and the differential circuit comprising at least a first and second thin film transistors,

wherein each of the first and second thin film transistors has a channel region comprising a polycrystalline semiconductor layer,

wherein a gate length of each of the first and second thin film transistors is 7 μm or longer; wherein the first and second thin film transistors are connected in parallel with each other and located in a cross arrangement; and

wherein a gate electrode of the first thin film transistor and a gate electrode of the second thin film transistor are connected to a same potential.

26. (Original) A semiconductor device according to claim 25, wherein the device

is selected from the group consisting of a liquid crystal display, an EL display a video camera, a digital camera, a projector, a projection TV, a goggle type display, a navigation system, a sound reproduction device, a note type personal computer, a game device, a portable information terminal, an image playback device having a recording medium.

27. (Original) A semiconductor device comprising:

an analog buffer comprising a source follower comprising a plurality of thin film transistors; and

cl a channel region of the respective thin film transistors, comprising a polycrystalline semiconductor layer;

wherein the respective thin film transistors is a multi-gate type;

wherein a gate length of the respective thin film transistors is 7 μm or longer and a gate width of the respective thin film transistors is 50 μm or longer;

wherein the plurality of thin film transistors are connected in parallel with each other, and

wherein gate electrodes of the plurality of thin film transistors are connected to a same potential.

28. (Original) A semiconductor device according to claim 27, wherein the device is selected from the group consisting of a liquid crystal display, an EL display, a video camera, a digital camera, a projector, a projection TV, a goggle type display, a navigation system, a sound reproduction device, a note type personal computer, a game device, a portable information terminal, an image playback device having a recording medium.
